

Transistors

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	50	–	–	V	I _C =50μA
Collector-emitter breakdown voltage	BV _{CE0}	50	–	–	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EB0}	5	–	–	V	I _E =50μA
Collector cutoff current	I _{CB0}	–	–	0.5	μA	V _{CB} =50V
Emitter cutoff current	I _{EB0}	–	–	0.5	μA	V _{EB} =4V
Collector-emitter saturation voltage	V _{CE(sat)}	–	–	0.3	V	I _C /I _B =10mA/1mA
DC current transfer ratio	h _{FE}	100	250	600	–	V _{CE} =5V, I _C =1mA
Transition frequency	f _T	–	250	–	MHz	V _{CE} =10mA, I _E =–5mA, f=100MHz *
Input resistance	R _i	3.29	4.7	6.11	kΩ	–

* Transition frequency of the transistor

●Packaging specifications

Type	Package	Taping		
	Code	T2R	TR	T148
	Basic ordering unit (pieces)	8000	3000	3000
EMG3	○	—	—	—
UMG3N	—	○	—	—
FMG3A	—	—	—	○

●Electrical characteristic curves

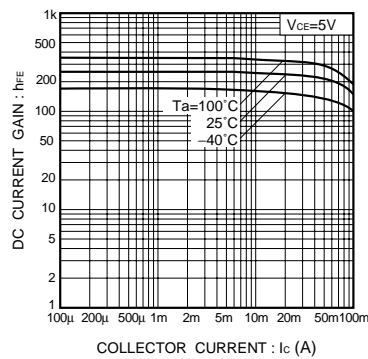


Fig.1 DC current gain vs. collector current

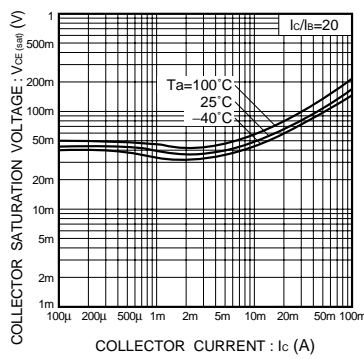


Fig.2 Collector-emitter saturation voltage vs. collector current



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